

BC857XQA series

45 V, 100 mA PNP general-purpose transistors

Rev. 1 — 26 August 2015

Product data sheet

1. Product profile

1.1 General description

PNP general-purpose transistors in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

Table 1. Product overview

Type number	Package			NPN complement
	NXP	JEITA	JEDEC	
BC857AQA	DFN1010D-3 (SOT1215)	-	-	BC847AQA
BC857BQA				BC847BQA
BC857CQA				BC847CQA

1.2 Features and benefits

- General-purpose transistors
- Three current gain selections
- Low package height of 0.37 mm
- Suitable for Automatic Optical Inspection (AOI) of solder joint
- AEC-Q101 qualified

1.3 Applications

- General-purpose switching and amplification
- Mobile applications

1.4 Quick reference data

Table 2. Quick reference data

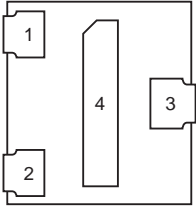
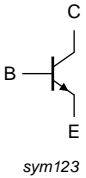
$T_{amb} = 25\text{ °C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-45	V
I_C	collector current		-	-	-100	mA
h_{FE}	DC current gain	$V_{CE} = -5\text{ V}; I_C = -2\text{ mA}$				
	BC857AQA		125	-	250	
	BC857BQA		220	-	475	
	BC857CQA		420	-	800	



2. Pinning information

Table 3. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base	 <p>Transparent top view</p>	
2	E	emitter		
3	C	collector		
4	C	collector		

3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
BC857AQA	DFN1010D-3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body: 1.1 × 1.0 × 0.37 mm	SOT1215
BC857BQA			
BC857CQA			

4. Marking

Table 5. Marking codes

Type number	Marking code
BC857AQA	00 11 10
BC857BQA	00 11 11
BC857CQA	01 00 01

4.1 Binary marking code description

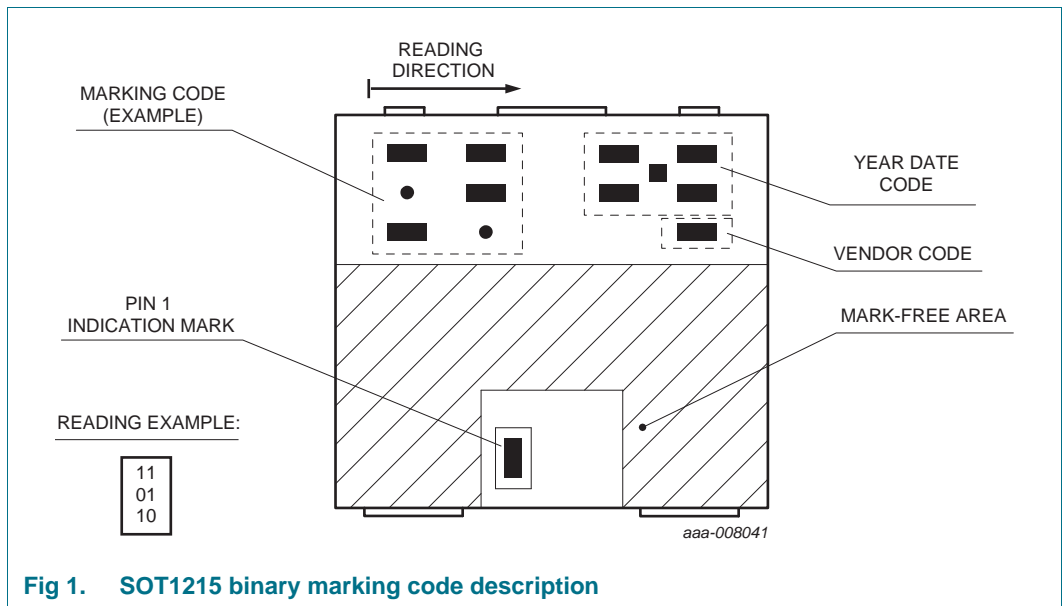


Fig 1. SOT1215 binary marking code description

5. Limiting values

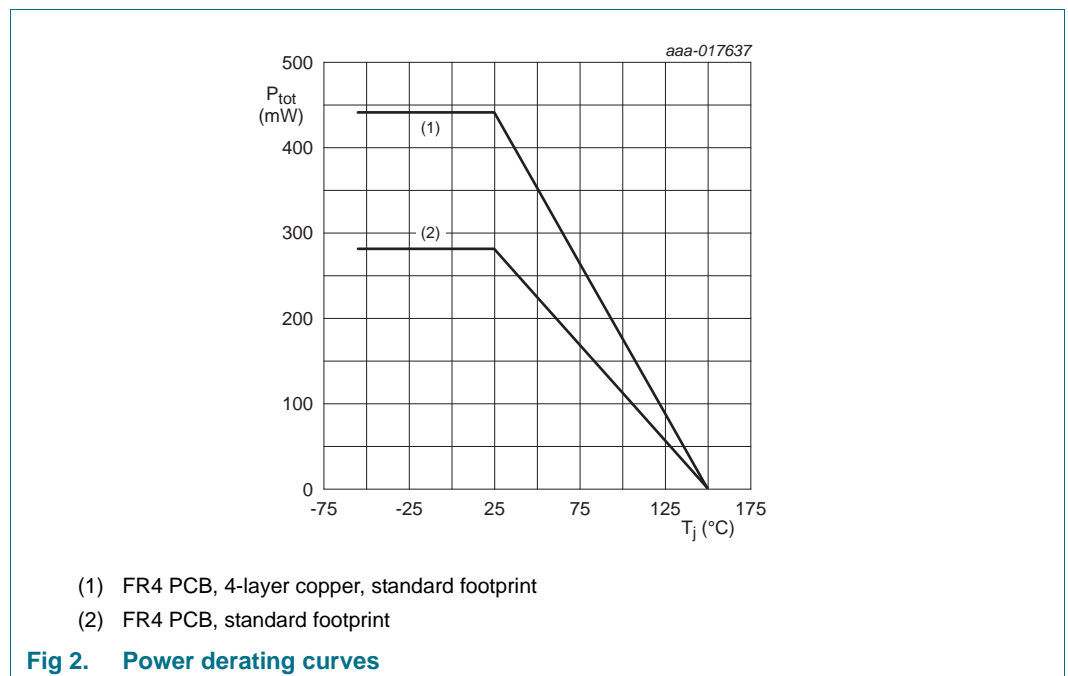
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V_{CBO}	collector-base voltage	open emitter	-	-50	V	
V_{CEO}	collector-emitter voltage	open base	-	-45	V	
V_{EBO}	emitter-base voltage	open collector	-	-6	V	
I_C	collector current		-	-100	mA	
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-200	mA	
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms	-	-100	mA	
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	280	mW
			[2]	-	440	mW
T_j	junction temperature		-	+150	°C	
T_{amb}	ambient temperature		-55	+150	°C	
T_{stg}	storage temperature		-65	+150	°C	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, 4-layer copper; tin-plated and standard footprint.



6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	446	K/W
			[2]	-	-	284	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, 4-layer copper; tin-plated and standard footprint.

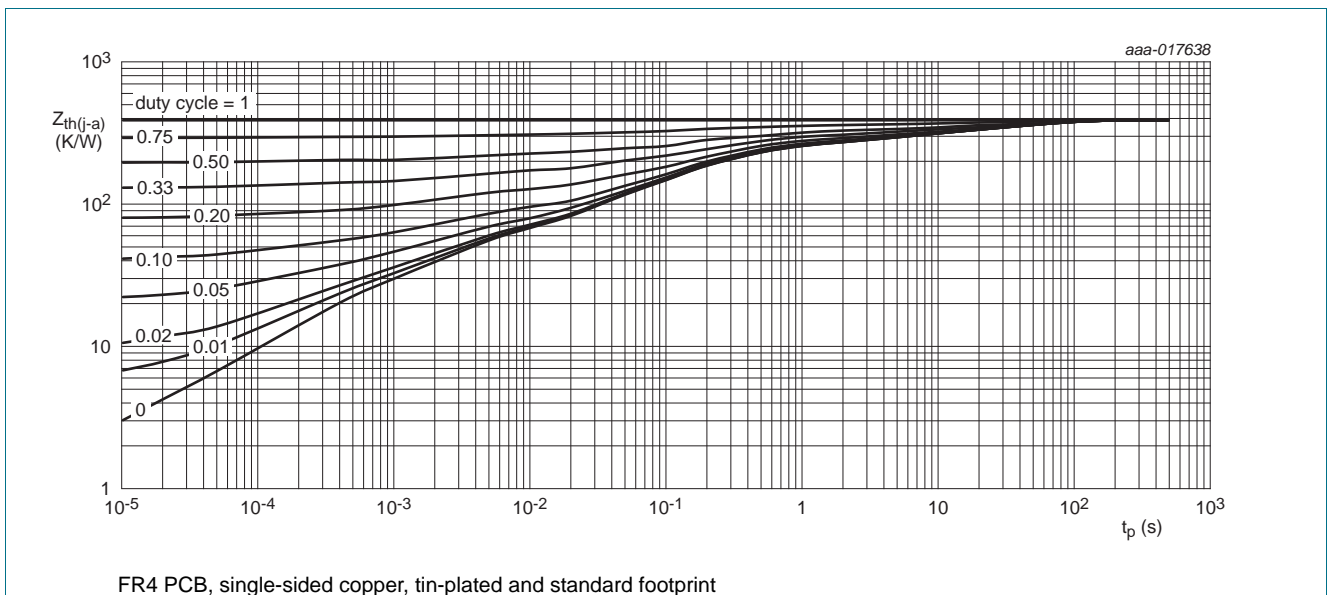


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

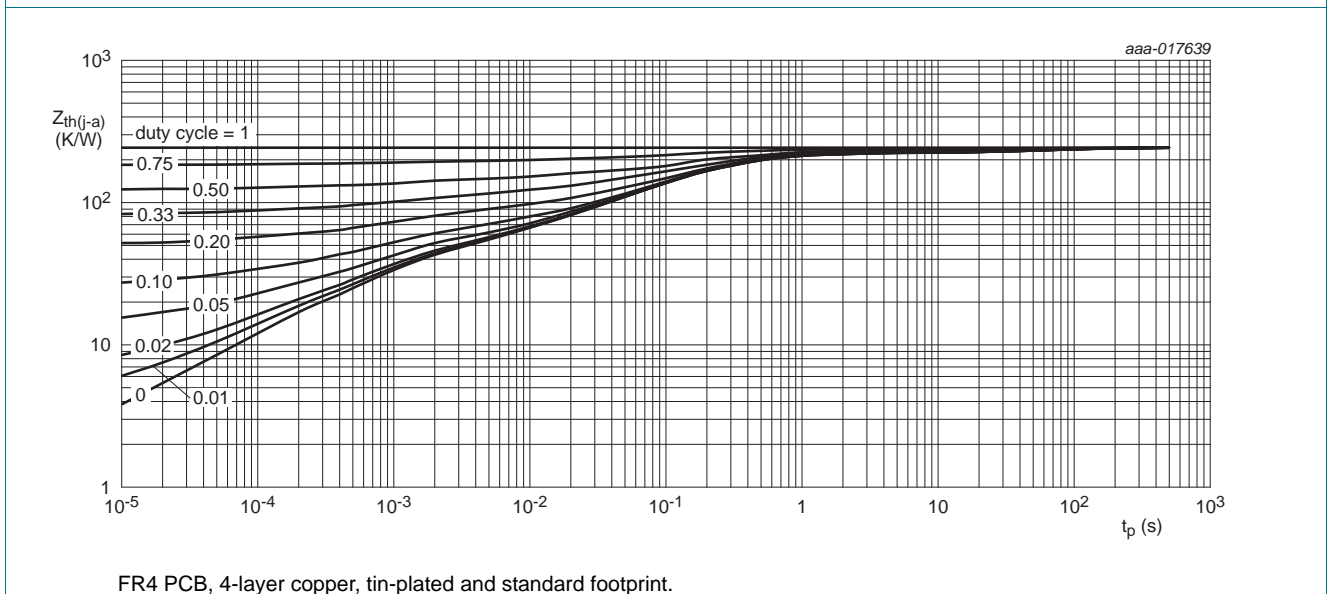


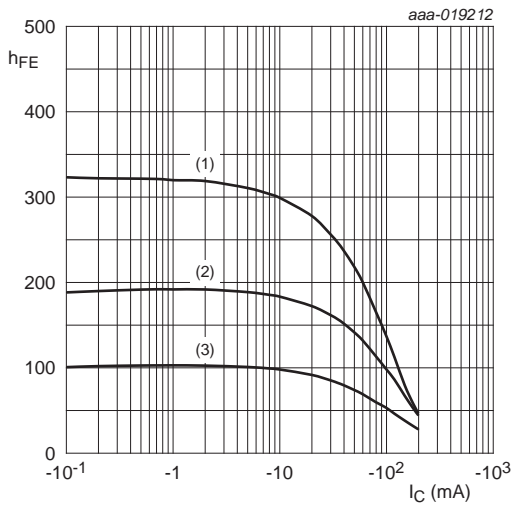
Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

7. Characteristics

Table 8. Characteristics
T_{amb} = 25 °C unless otherwise specified.

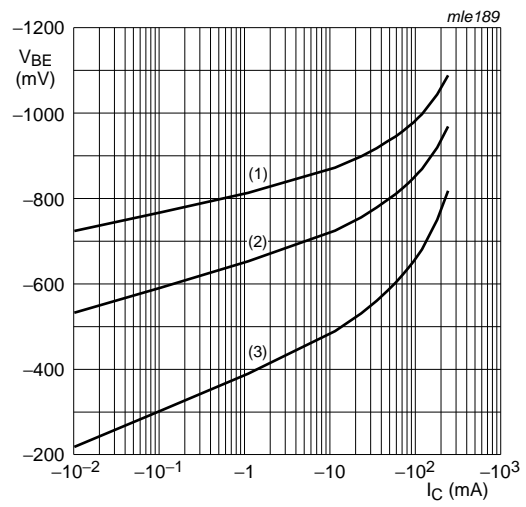
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{CBO}	collector-base cut-off current	V _{CB} = -30 V; I _E = 0 A	-	-	-15	nA
		V _{CB} = -30 V; I _E = 0 A; T _j = 150 °C	-	-	-5	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -5 V; I _C = -2 mA				
	BC857AQA		125	-	250	
	BC857BQA		220	-	475	
	BC857CQA		420	-	800	
V _{CEsat}	collector-emitter saturation voltage	I _C = -10 mA; I _B = -0.5 mA	-	-	-200	mV
		I _C = -100 mA; I _B = -5 mA [1]	-	-	-400	mV
V _{BEsat}	base-emitter saturation voltage	I _C = -10 mA; I _B = -0.5 mA	-	-760	-	mV
		I _C = -100 mA; I _B = -5 mA [1]	-	-900	-	mV
V _{BE}	base-emitter voltage	I _C = -2 mA; V _{CE} = -5 V	-600	-	-750	mV
		I _C = -10 mA; V _{CE} = -5 V	-	-	-820	mV
f _T	transition frequency	V _{CE} = -5 V; I _C = -10 mA; f = 100 MHz	100	-	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = i _e = 0 A; f = 1 MHz	-	-	2.5	pF
C _e	emitter capacitance	V _{EB} = -0.5 V; I _C = i _c = 0 A; f = 1 MHz	-	10	-	pF
NF	noise figure	I _C = -200 μA; V _{CE} = -5 V; R _S = 2 kΩ; f = 1 kHz; B = 200 Hz	-	-	10	dB

[1] Pulse test: t_p ≤ 300 μs; δ = 0.02



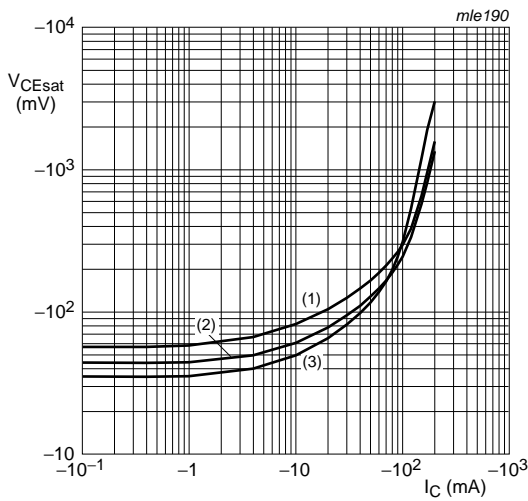
$V_{CE} = -5\text{ V}$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 5. BC857AQA: DC current gain as a function of collector current; typical values



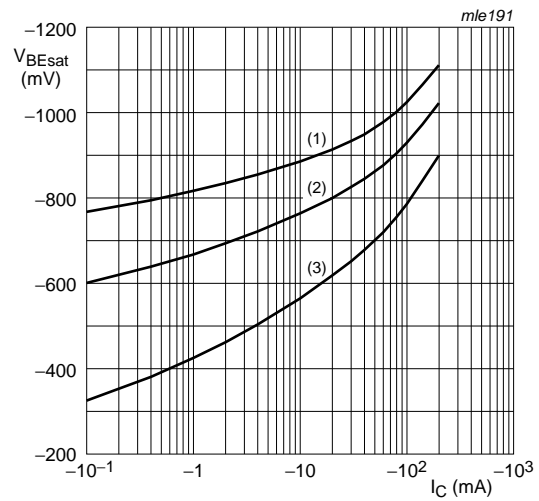
$V_{CE} = -5\text{ V}$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

Fig 6. BC857AQA: Base-emitter voltage as a function of collector current; typical values



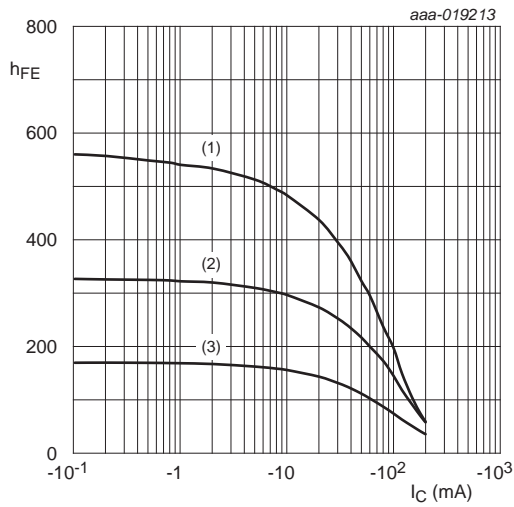
$I_C/I_B = 20$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 7. BC857AQA: Collector-emitter saturation voltage as a function of collector current; typical values



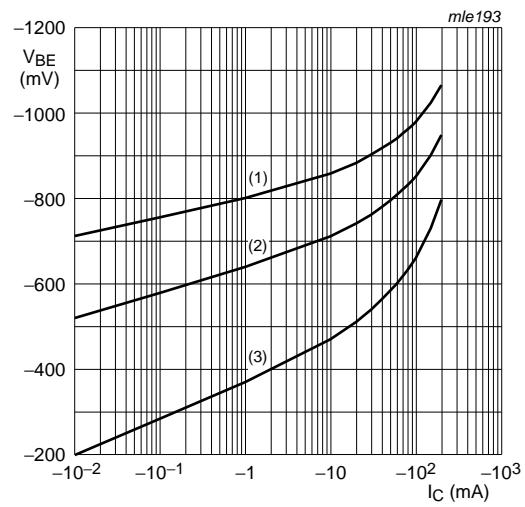
$I_C/I_B = 20$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

Fig 8. BC857AQA: Base-emitter saturation voltage as a function of collector current; typical values



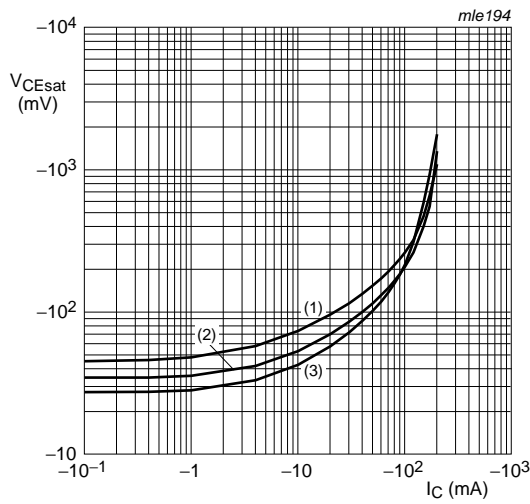
$V_{CE} = -5\text{ V}$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 9. BC857BQA: DC current gain as a function of collector current; typical values



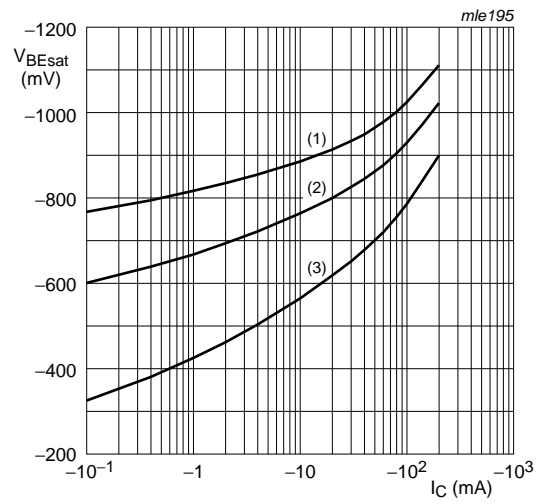
$V_{CE} = -5\text{ V}$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

Fig 10. BC857BQA: Base-emitter voltage as a function of collector current; typical values



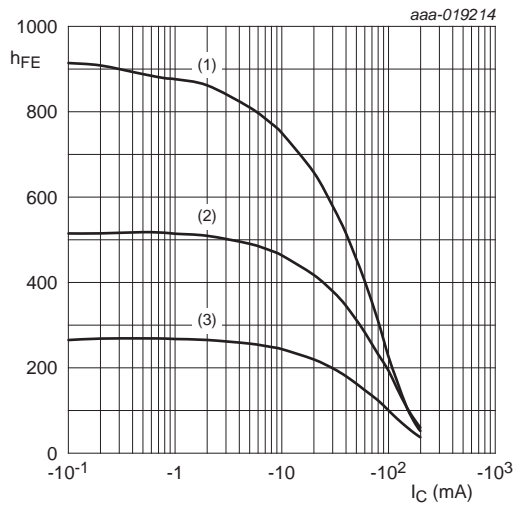
$I_C/I_B = 20$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 11. BC857BQA: Collector-emitter saturation voltage as a function of collector current; typical values



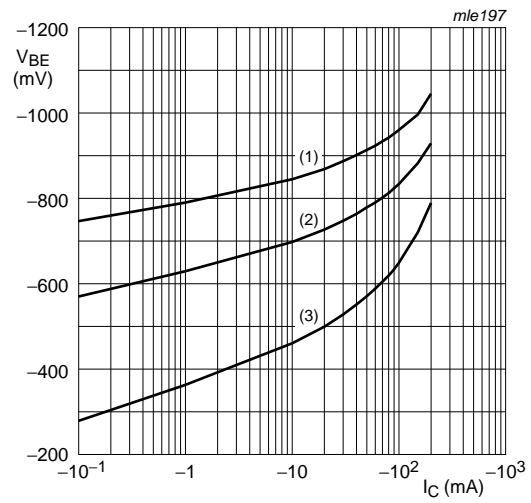
$I_C/I_B = 20$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

Fig 12. BC857BQA: Base-emitter saturation voltage as a function of collector current; typical values



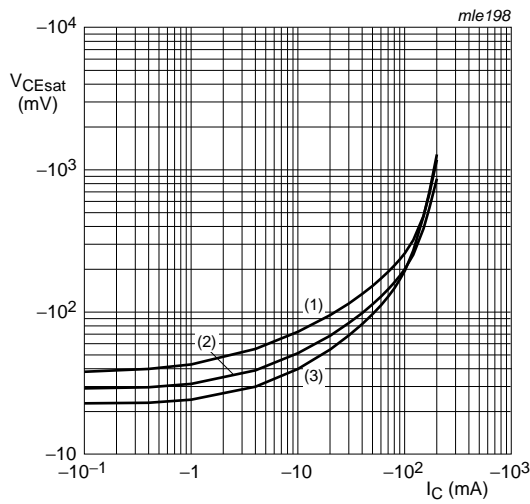
$V_{CE} = -5\text{ V}$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 13. BC857CQA: DC current gain as a function of collector current; typical values



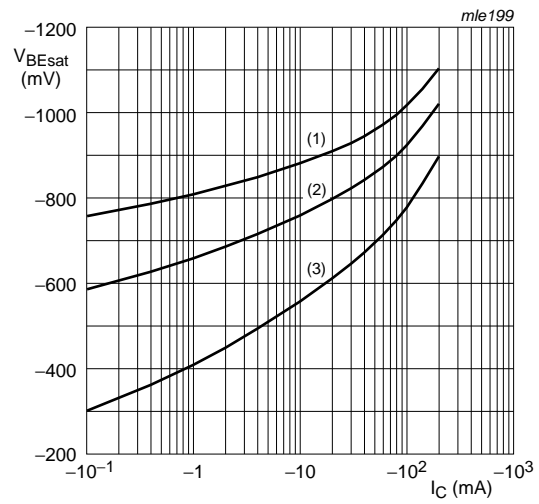
$V_{CE} = -5\text{ V}$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

Fig 14. BC857CQA: Base-emitter voltage as a function of collector current; typical values



$I_C/I_B = 20$
 (1) $T_{amb} = 150\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 15. BC857CQA: Collector-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 150\text{ °C}$

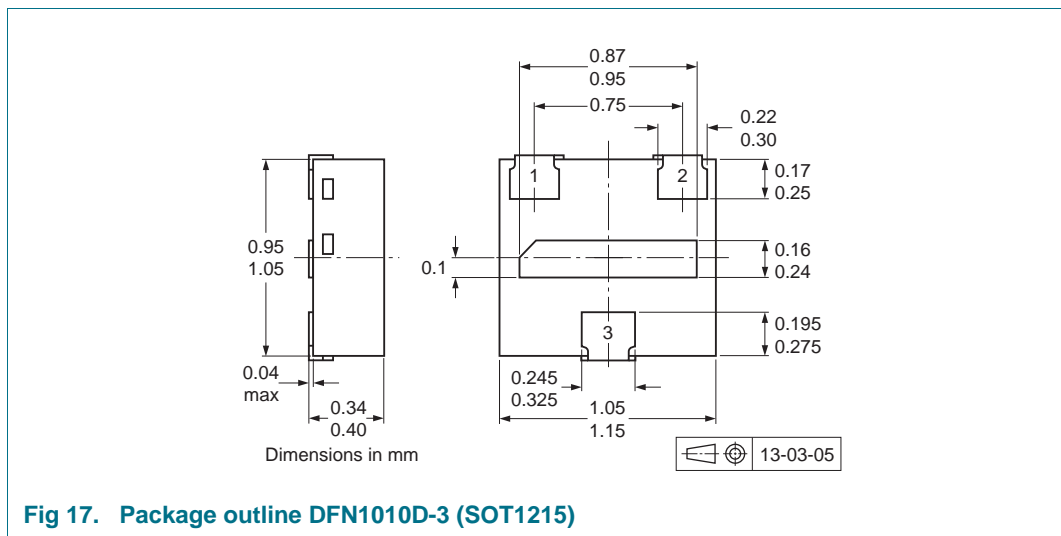
Fig 16. BC857CQA: Base-emitter saturation voltage as a function of collector current; typical values

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Soldering

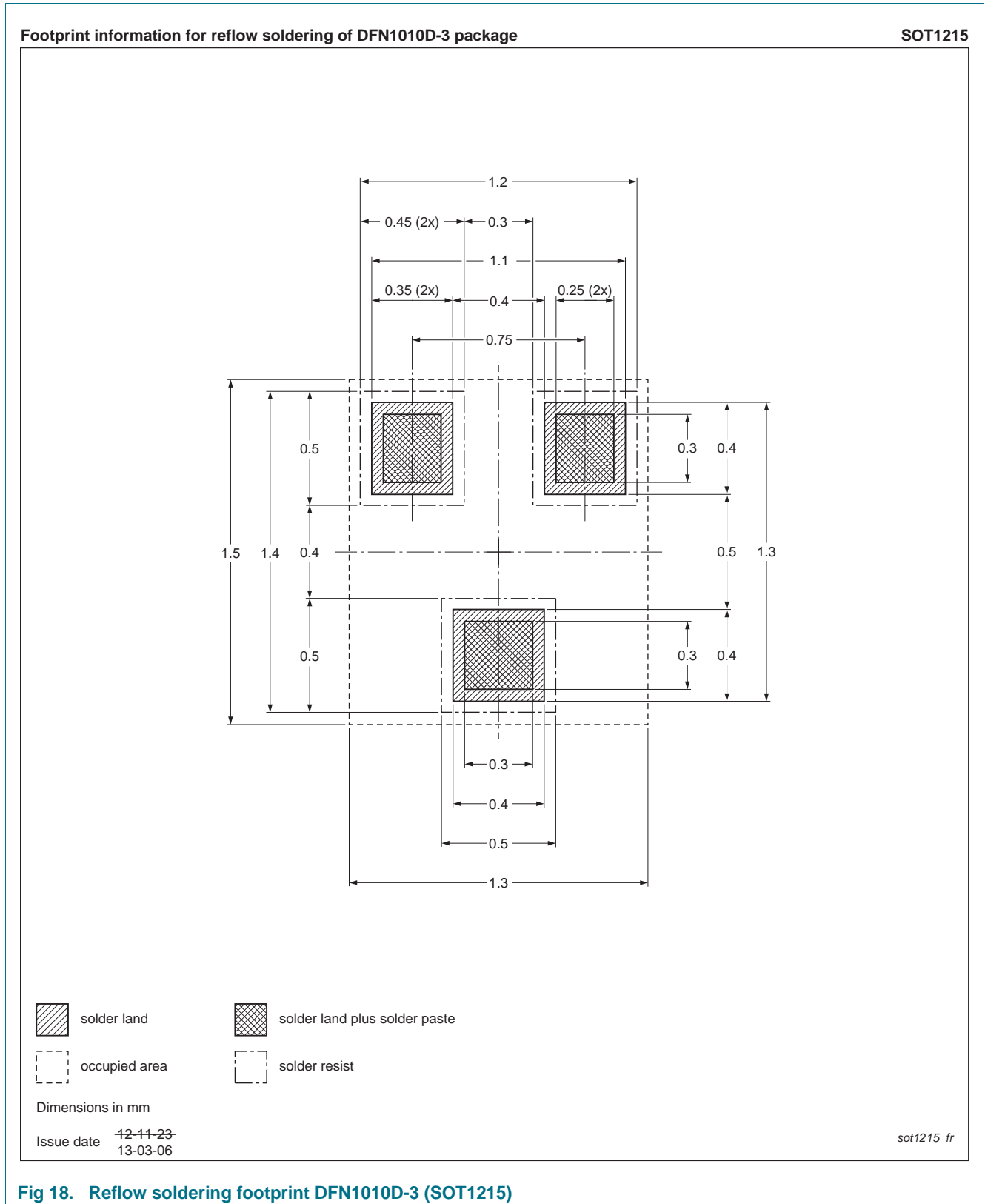


Fig 18. Reflow soldering footprint DFN1010D-3 (SOT1215)

11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC857XQA_SER v.1	20150826	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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